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ning of each regular issue of the PCT Gazette.*

(54) **Title:** CLEANING COMPOSITION, METHOD OF CLEANING SEMICONDUCTOR SUBSTRATE, AND METHOD OF  
FORMING WIRING ON SEMICONDUCTOR SUBSTRATE

(57) **Abstract:** A cleaning composition comprises at least quaternary ammonium hydroxide, a water-soluble organic solvent, water,  
an anticorrosive, and potassium hydroxide of 1 mass percent or less of a total amount of the solution. This cleaning composition can  
singly and effectively remove a photoresist film, a buried material, a metallic residue from the surface of a semiconductor substrate.

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